

Citations for Ion : Gd

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1966	VanLint, V. A. J. Wyatt, M. E. Schmitt, R. A. Suffredini, C. S. Nichols, D. K. 'Range of Photoparticle Recoil Atoms on Solids' <i>Phys. Rev., 147, 242-48 (1966)</i> <i>Comment : R. (.001- 5 epsilon) Ti, Sc, Cr, Fe, Mn, Ni, Co, Ge, Zr, Y, Sr, Mo, Rh, Pd, Ag, Cd, Sn, Gd, Ta, Au, Th -> Al, Cu</i>	1966-VanL
1974	Scholten, P. Skokan, M. Kemper, K. W. Moulton, W. G. 'Range and Distributin of Gd Implanted in Nb as Determined by 16O Backscatter Method' <i>Bull. Am. Phys. Soc., 19, 1117 (1974)</i> <i>Comment : R. 50-150 keV Gd -> Nb</i>	1974-Scho
1975	Hvelplund, P. 'Energy Loss and Straggling of 100-500 keV 90Th, 82Pb, 80Hg, and 64Gd in H2' <i>Phys. Rev. A, 11, 1921-27 (1975)</i> <i>Comment : S, dS. 100-500 keV Gd, Hg, Pb, Th -> H2</i>	1975-Hvel
1975	Kiselevich, M. Lyatushinski, A. Zhuk, V. Osipenko, B. P. 'Implantation of Heavy Ions into Silicon Single Crystals' <i>Fiz. Tverd. Tela, 17, 1080-84 (1975). [Engl. Trans. Sov. Phys. Solid State, 17, 687-89 (1975)]</i> <i>Comment : R, dR. 45 keV Sr, Ba, Ce, Nd, Eu, Gd, Tb, Er, Tm, Lu -> Si (Cryst. Chann. And Random)</i>	1975-Kise
1976	Baragiola, R. A. Chivers, D. Dodds, D. Grant, W. A. Williams, J. S. 'Ranges in Silicon of Ions with Atomic Numbers 62 <= Z1 <= 66 at 100 keV' <i>Phys. Letters A, 56, 371=73 (1976)</i> <i>Comment : R, dR. 100 keV 152Sm, 153Eu, 157Gd, 159Tb, 164Dy -> Si</i>	1976-Bara
1976	Scholten, P. D. Skokan, M. R. Kemper, K. W. Moulton, W. G. 'Range and Distribution of Gd Ions Implanted in Nb Thin Films' <i>Phys. Rev. B, 13, 42-44 (1976)</i> <i>Comment : R,dR. 50-150 keV Gd -> Nb</i>	1976-Scho
1976	Sood, D. K. Dearnaley, G. 'Ion-Implanted Surface Alloys in Copper and Aluminum' <i>G. Carter, J. S. Colligon, W. A. Grant (Ed.): Appl. of Ion Beams to Materials. Inst. of Physics Conf. Ser. No. 28, 169-203 (1976)</i> <i>Comment : R. (150-300) keV Au, Mo, Bi, Ta, Mo, Gd, Bi, Cu, Rb, Ru, Cs, Ce, Eu, Ag, Cu, Se, Au -> Cu; Rb, Cd, Cs -> Al.</i>	1976-Sood
1978	Combasson, J. L. Farmery, B. W. McCulloch, D. Neilson, G. W. Thompson, M. W. 'Heavy Ion Ranges in Aluminum and Silicon' <i>Rad. Effects, 36, 149-156 (1978)</i> <i>Comment : R, dR. 20-250 keV Cs, La, Pr, Eu, Tb, Dy, Ho, Er, Lu, Hf, Pt, Au, Tl, Pb, Bi -> Al; Sm, Eu, Gd, Tb, Dy -> Si</i>	1978-Comb

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1986	Geyer, E. Reschke, D. Freitag, K. 'Z1 Stopping Power Oscillation in the Nuclear Stopping Regime as Obtained by Time-of-Flight Spectroscopy of Heavy Ions in Hydrogen' <i>Nucl. Inst. Methods, B15, 81-85 (1986)</i> <i>Comment : S. Heavy Ions (49-65) at 26 - 90 keV -> H2 (gas)</i>	1986-Geye
1987	Freitag, K. Reschke, D. Geyer, E. 'Stopping Power Measurements for Low Energy Ions in Gases by Time-of-Flight Spectroscopy' <i>Nucl. Inst. Methods, B27, 344-352 (1987)</i> <i>Comment : S. Heavy Ions (49-65) at 27 - 90 keV -> H2 (gas)</i>	1987-Frei